

N-Ch MOSFET

Description

The WSD1614DN uses advanced trench technology to provide excellent RDS(ON), low gate charge and operation with gate voltages as low as 1.8V.

This device is suitable for use as a Battery protection or in other Switching application.

Features

ESD:1.5KV

High power and current handing capability

Lead free product is acquired Surface mount package

Product Summery

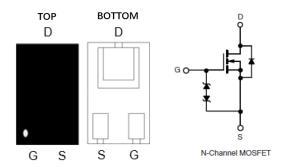
BVDSS	RDSON	ID
20V	230m Ω	1.4A

Application

Battery protection

Load switch

DFN1.0X0.6-3L Pin Configuration



Absolute Maximum Ratings @TA=25℃ unless otherwise noted

Symbol	Parameter	Ratin	Unit	
VDS	Drain-Source Voltage		20	V
VGS	Gate-Source Voltage		±8	V
ID	Drain Current (Continuous) *AC	TA=25°C	1.4	Α
		TA=70°C	1.1	А
IDM	Drain Current (Pulse) *B	3	А	
PD	Power Dissipation	TC=25°C	0.55	W
TJ/TSTG	Operating Temperature/ Storage Temperature		-55~150	${\mathbb C}$

Thermal Resistance Ratings

Symbol	Parameter	Max	Unit	
RthJA	Maximum Junction-to-Ambient	Steady-State	180	°C/W

N-Ch MOSFET

Electrical Characteristics @TA=25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
V(BR)DSS	Drain-Source Breakdown Voltage	Vgs = 0V, ID= 250µA	20	-		V
IDSS	Zero Gate Voltage Drain Current	V _{DS} = 16V, V _{GS} = 0V			1	μA
Vgs(th)	Gate Threshold Voltage	Vgs = Vps, Ips= 250µA	0.4		1	V
Igss	Gate Leakage Current	Vgs= 8V, Vps=0V			10	μA
	Drain-Source On-state Resistance	V _G S = 4.5V, I _D = 0.55A			230	mΩ
RDS(on)		Vgs = 2.5V, ID = 0.45A			305	mΩ
		Vgs = 1.8V, ID = 0.35A			455	mΩ
VsD	Diode Forward Voltage	Isp= 0.35A , Vgs=0V			1.2	V
Is	Diode Forward Current *AC	T _A =25°C			0.58	Α
Qg	Total Gate Charge	Vgs=4.5V, Vbs=10V, ————————————————————————————————————		2		nC
Qgs	Gate-Source Charge			0.3		nC
Qgd	Gate-Drain Charge	TID=TA		0.3		nC
td (on)	Turn-on Delay Time			1.2		ns
tr	Turn-on Rise Time	V _{GS} =4.5V, V _{DS} =10V, R _G =6 , I _D =2A		25		ns
td(off)	Turn-off Delay Time			14		ns
tf	Turn-Off Fall Time			15		ns
Ciss	Input Capacitance	-V _{DS} =10V,		43		pF
Coss	Output Capacitance	V _{GS} =10V, V _{GS} =0V, f=1.0MHz		9		pF
Crss	Reverse Transfer Capacitance	T=1.UIVIMZ		6		pF

Note:

A: The value of RθJA is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper,

in a still air environment with TA=25 $^{\circ}\text{C}.$ The value in any given application depends

on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

C: The current rating is based on the t≤ 10s junction to ambient thermal resistance rating.



Typical Performance Characteristics ((TJ = 25 °C, unless otherwise noted))

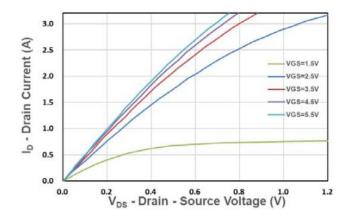


Figure 1. Output Characteristics

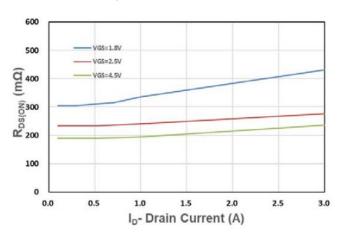


Figure 2. On-Resistance vs. I

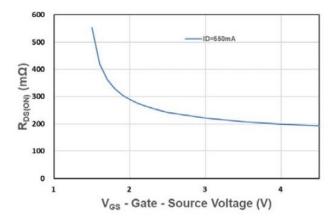


Figure 3. On-Resistance vs. VGS

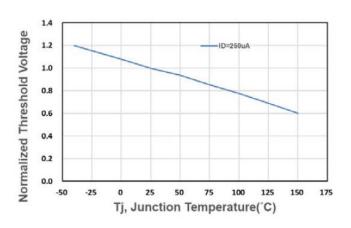


Figure 4. Gate Threshold Voltage

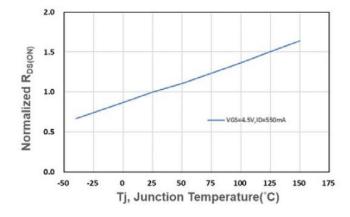


Figure 5. Drain-Source On Resistance

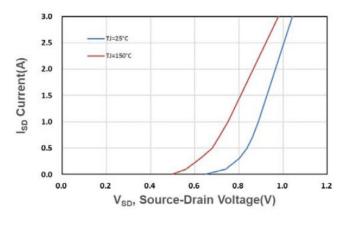


Figure 6. Source-Drain Diode Forward



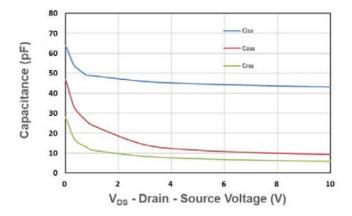


Figure 7. Capacitance

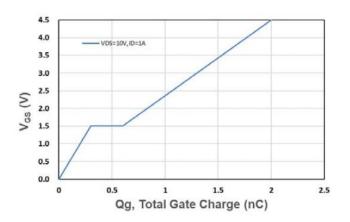


Figure 8. Gate Charge Characteristics

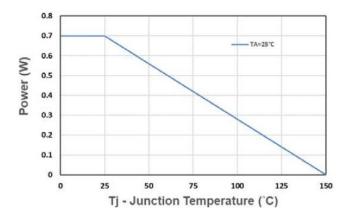


Figure 9. Power Dissipation

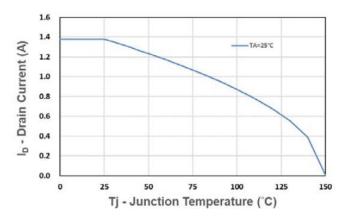


Figure 10. Drain Current

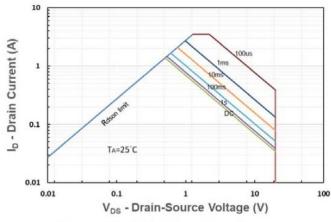


Figure 11. Safe Operating Area

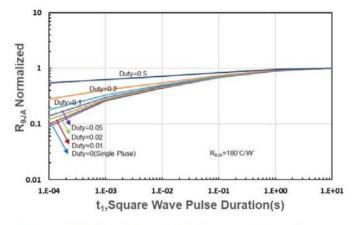
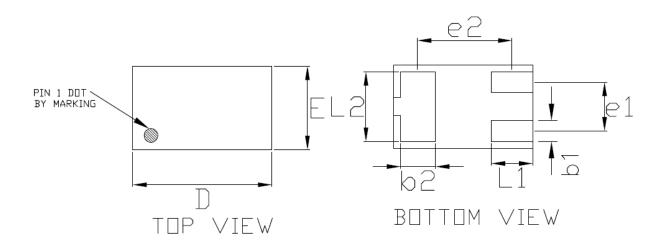
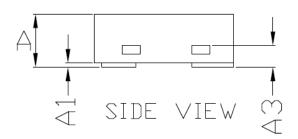


Figure 12. Reja Transient Thermal Impedance



DFN1.0*0.6-3L





COMMON DIMENSIONS(MM)				
PKG.	X1:EXTREME THIN			
REF.	MIN.	N□M.	MAX	
Α	>0.40	_	0,50	
A1	0.00	_	0,05	
A3	0.125 REF.			
D	0.95	1.00	1.05	
E	0,55	0.60	0.65	
k1	0,10	0,15	0,20	
b2	0.20	0.25	0,30	
L1	0,20	0.30	0.40	
L2	0.40	0.50	0,60	
e1	0,35 BSC			
e2	0,675 BSC			

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